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2N3691

NPN SMALL SIGNAL GENERAL PURPOSE AMPLIFIER

ABSOLUTE MAXIMUM RATINGS [Note 1]

Maximum	Temperatures
Storago	Compositions

Storage Temperature -55°C to +125°C

Operating Junction Temperature 125°C Maximum

Soldering Temperature (10 sec time limit) 260°C Maximum

Maximum Power Dissipation

Total Dissipation at 25°C Case Temperature [Note 2] 0.5 Watt at 65°C Case Temperature [Note 2] 0.3 Watt at 25°C Ambient Temperature [Note 2] 0.2 Watt

Maximum Voltages

 $\begin{array}{lll} {\rm V_{CBO}} & {\rm Collector\ to\ Base\ Voltage} & 35\ {\rm Volts} \\ \\ {\rm V_{CEO}} & {\rm Collector\ to\ Emitter\ Voltage\ [\,Note\ 3\,]} & 25\ {\rm Volts} \\ \\ {\rm V_{EBO}} & {\rm Emitter\ to\ Base\ Voltage} & 4.0\ {\rm Volts} \\ \end{array}$

PHYSICAL DIMENSIONS
In accordance with JEDEC (TO-106) outline

.222
.192
.240
MAX.

3 LEADS .500 MIN.
.500

ELECTRICAL CHARACTERISTICS (25°C Free Air Temperature unless otherwise noted)

Symbol	Characteristic	Min.	Max.	Units	Test Conditions
h _{FE}	DC Pulse Current Gain [Note 4]	40	160		$I_{C} = 10 \text{ mA} V_{CE} = 1.0 \text{ V}$
^h fe	High Frequency Current Gain (f = 100 MHz)	2.0			
V _{CE} (sat)	Collector Saturation Voltage		0.7	Volts	C CE 22
VBE (sat)	Base Saturation Voltage		0.9	Volts	$I_{C} = 10 \text{ mA} I_{B} = 1.0 \text{ mA}$
I _{СВО}	Collector Cutoff Current		50	n A	$I_C = 10 \text{ mA} I_B = 1.0 \text{ mA}$
I _{CBO} (65°C)	Collector Cutoff Current		5.0	μΛ	$I_{E} = 0 \qquad V_{CB} = 30 \text{ V}$ $I_{CB} = 30 \text{ V}$
C _{obo}	Common-Base, Open-Circuit Output Capacitance		6.0	pF	E CB
V _{CEO} (sust)	Collector to Emitter Sustaining Voltage [Notes 3 and 4]	25	·	Volts	$I_C = 10 \text{ mA} I_R = 0$
вv _{сво}	Collector to Base Breakdown Voltage	35		Volts	(pulsed) $I_{C} = 100 \mu A I_{D} = 0$
BV _{EBO}	Emitter to Base Breakdown Voltage	4.0		Volts	$I_{C} = 0$ $I_{E} = 0$ I_{A}

NOTES:

- (1) These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
- (2) These ratings give a maximum junction temperature of 125°C and junction-to-case thermal resistance of 200°C/Watt (derating factor of 5.0 mW/°C); junction-to-ambient thermal resistance of 500°C/Watt (derating factor of 2.0 mW/°C).
- (3) Rating refers to a high-current point where collector-to-emitter voltage is lowest.
- (4) Pulse Conditions: length = 300 μ s; duty cycle = 1%.

